



NPN SILICON RF TRANSISTOR NE85618 / 2SC5011

NPN EPITAXIAL SILICON RF TRANSISTOR FOR HIGH-FREQUENCY LOW-NOISE AMPLIFICATION 4-PIN SUPER MINIMOLD

FEATURES

- High Gain Bandwidth Product ($f_T = 6.5$ GHz TYP.)
- Low Noise, High Gain
- Low Voltage Operation
- 4-pin super mini mold Package

★ ORDERING INFORMATION

Part Number	Quantity	Supplying Form
NE85618-A 2SC5011	50 pcs (Non reel)	• 8 mm wide embossed taping • Pin 3 (Base), Pin 4 (Emitter) face to perforation side of the tape
NE85618-T1-A 2SC5011-T1	3 kpcs/reel	

Remark To order evaluation samples, contact your nearby sales office.

The unit sample quantity is 50 pcs.

ABSOLUTE MAXIMUM RATINGS ($T_A = +25^\circ\text{C}$)

Parameter	Symbol	Ratings	Unit
Collector to Base Voltage	V_{CBO}	20	V
Collector to Emitter Voltage	V_{CEO}	12	V
Emitter to Base Voltage	V_{EBO}	3	V
Collector Current	I_C	100	mA
Total Power Dissipation	P_{tot} ^{Note}	150	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-65 to +150	$^\circ\text{C}$

Note Free air

Caution: Observe precautions when handling because these devices are sensitive to electrostatic discharge

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version.

ELECTRICAL CHARACTERISTICS (T_A = +25°C)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
DC Characteristics						
Collector Cut-off Current	I _{CBO}	V _{CB} = 10 V, I _E = 0 mA	–	–	1.0	μA
Emitter Cut-off Current	I _{EBO}	V _{EB} = 1 V, I _C = 0 mA	–	–	1.0	μA
DC Current Gain	h _{FE} ^{Note 1}	V _{CE} = 10 V, I _C = 20 mA	50	120	250	–
RF Characteristics						
Gain Bandwidth Product	f _T	V _{CE} = 10 V, I _C = 20 mA	–	6.5	–	GHz
Insertion Power Gain	S _{21e} ²	V _{CE} = 10 V, I _C = 20 mA, f = 1.0 GHz	11	13	–	dB
Noise Figure	NF	V _{CE} = 10 V, I _C = 7 mA, f = 1.0 GHz	–	1.1	2.0	dB
Reverse Transfer Capacitance	C _{re} ^{Note 2}	V _{CB} = 10 V, I _E = 0 mA, f = 1.0 MHz	–	0.5	0.9	pF

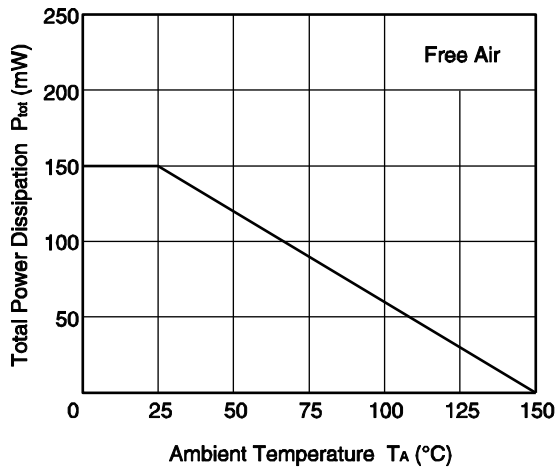
- Notes 1.** Pulse measurement: PW ≤ 350 μs, Duty Cycle ≤ 2%
2. Collector to base capacitance when the emitter grounded

h_{FE} CLASSIFICATION

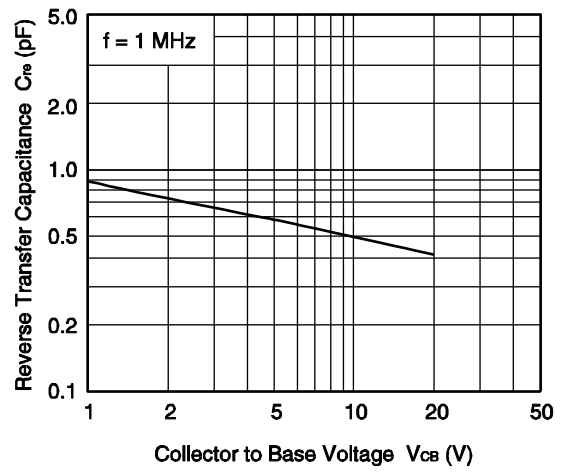
Rank	EB	FB	GB
Marking	R26	R27	R28
h _{FE} Value	50 to 100	80 to 160	125 to 250

TYPICAL CHARACTERISTICS ($T_A = +25^\circ\text{C}$, unless otherwise specified)

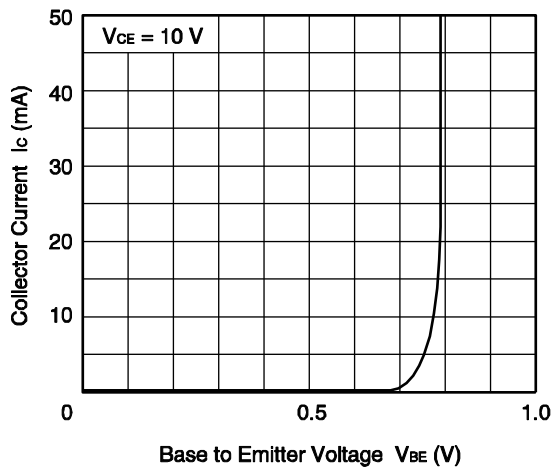
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



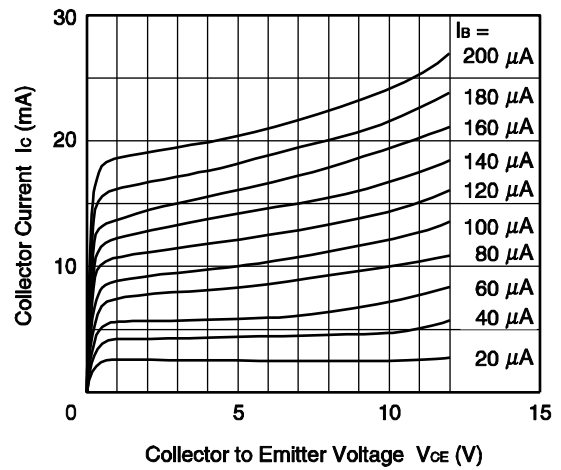
REVERSE TRANSFER CAPACITANCE vs. COLLECTOR TO BASE VOLTAGE



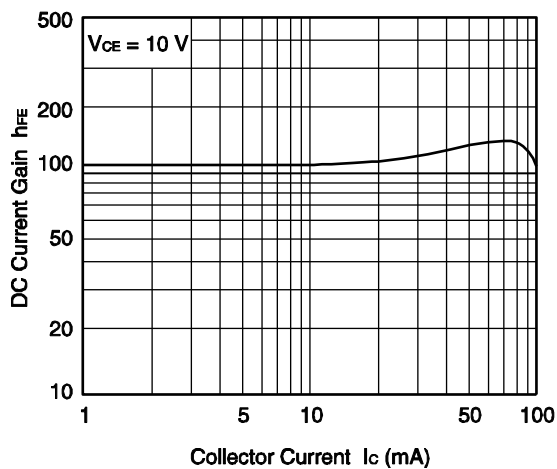
COLLECTOR CURRENT vs. BASE TO EMITTER VOLTAGE



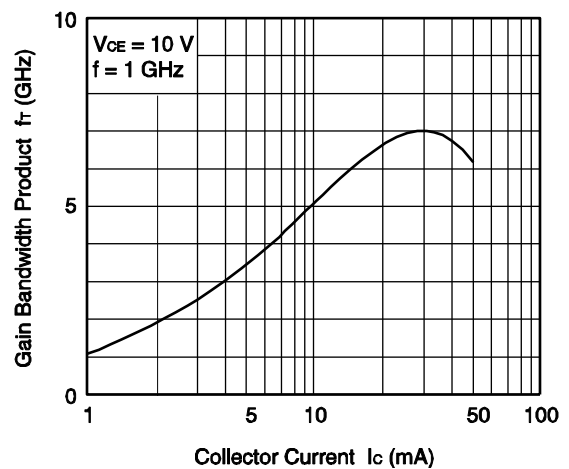
COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



DC CURRENT GAIN vs. COLLECTOR CURRENT

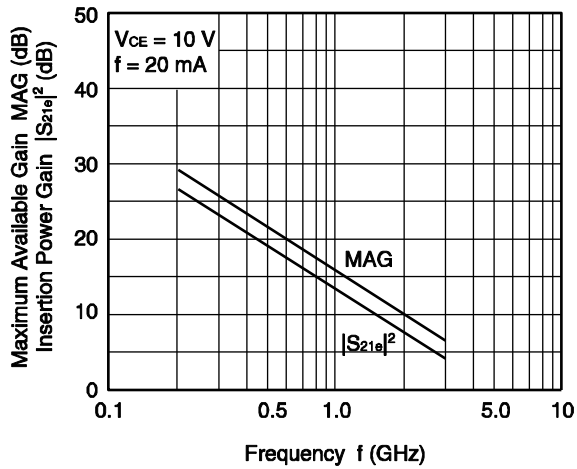


GAIN BANDWIDTH PRODUCT vs. COLLECTOR CURRENT

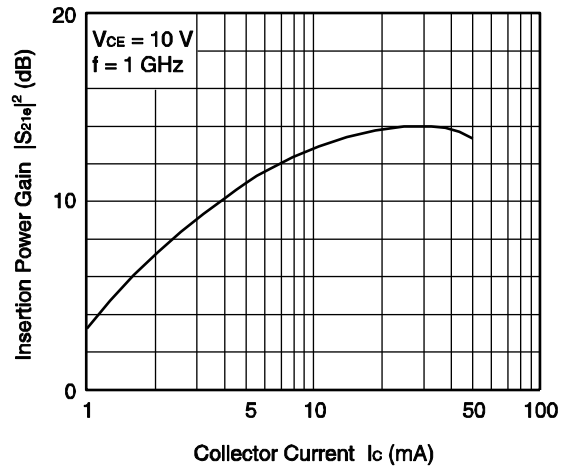


Remark The graphs indicate nominal characteristics.

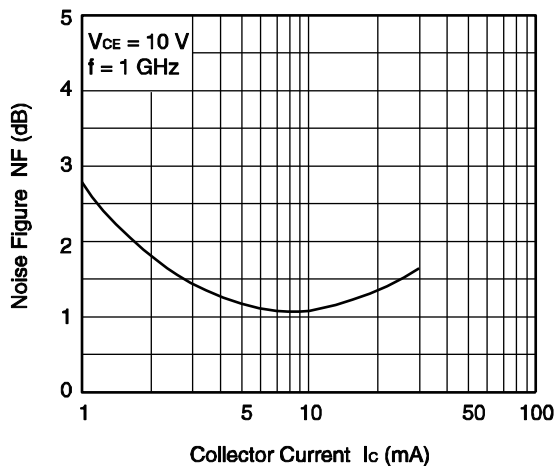
MAXIMUM AVAILABLE GAIN/INSERTION POWER GAIN vs. FREQUENCY



INSERTION POWER GAIN vs. COLLECTOR CURRENT



NOISE FIGURE vs. COLLECTOR CURRENT



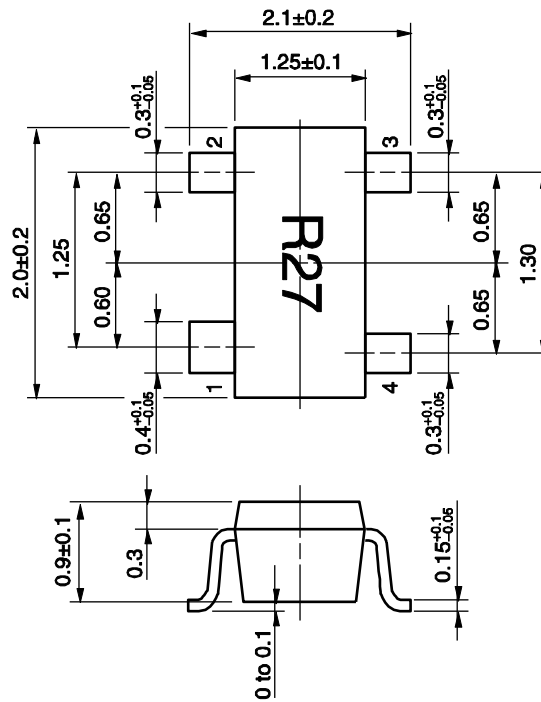
Remark The graphs indicate nominal characteristics.

★ **S-PARAMETERS**

- S-parameters and noise parameters are provided on our Web site in a format (S2P) that enables the direct import of the parameters to microwave circuit simulators without the need for keyboard inputs.
- Click here to download S-parameters.
- [RF and Microwave] ® [Device Parameters]
- URL <http://www.necel.com/microwave/en/>

★ **PACKAGE DIMENSIONS**

4-PIN SUPER MINIMOLD (UNIT: mm)



PIN CONNECTIONS

- 1. Collector
- 2. Emitter
- 3. Base
- 4. Emitter